

AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 1, line 11, as follows:

Recently, the operation frequency of a semiconductor integrated circuit device has become[[s]] very high. ~~[[and a]]~~A wiring line region allocated for power supply wiring lines and ground wiring lines tends to ~~increase more~~ have a greater increase in operation frequency. Therefore, it becomes easy for an internal circuit of the semiconductor integrated circuit device to ~~result in destruction~~ be destroyed if a voltage surge is momentary applied or a high voltage is ~~always~~ consistently applied when the semiconductor integrated circuit device is actually used. In order to avoid the destruction of the inner circuit due to application of the voltage surge or the high voltage, a protection circuit is conventionally connected with input/output terminals to improve the voltage endurance of the internal circuit. As one of such techniques, Japanese Laid Open Patent Application (JP-P2002-289704A) describes a technique, in which boron regions of different depths are formed as P-wells between two N-wells provided in a P-type substrate apart from each other. These regions are formed through ~~twice of two~~ two ion implantations using a same mask[[,]]. ~~The and the~~ deeper boron region is deeper than the two N-wells to increase the breakdown voltage and to suppress leak between the two N-wells at the same time.

Please amend the paragraph beginning at page 2, line 8, as follows:

However, when the interval between the two N-wells is [[in]] of order of submicron, it is not possible to keep the breakdown voltage between the two N-wells high in the P-well structure of the above Japanese Laid Open Patent Application (JP-P2002-289704A).

Please amend the paragraph beginning at page 3, line 23, as follows:

Also, a semiconductor device is disclosed in Japanese Laid Open Patent Application (JP-A-Heisei 2-148852). In the semiconductor device of this conventional example, a gate electrode is partially provided on a semiconductor substrate directly or via a gate insulating film. A drain region and a source region are provided on the gate electrode in the semiconductor substrate surface. An insulating film is provided in a wall region of the drain region other than a lower region below the drain region and a channel region below the gate electrode. An impurity dope region is provided at a predetermined depth straight[[ly]] below the gate electrode. [[to have]] This impurity dope region has the same conductive type as the semiconductor substrate and an impurity concentration higher than that of the semiconductor substrate. The peak impurity concentration position of the impurity dope region is within 0.8 μm from the semiconductor substrate surface.

Please amend the paragraph beginning at page 5, line 22, as follows:

Also, a minimum of the impurity peak concentration of the fourth region is $(1-s)*1.4E16$ (~~atom/cm⁴~~) (atom/cm³), where the predetermined interval is s.

Please amend the paragraph beginning at page 10, line 22, as follows:

From the impurity distributions, it could be understood that a boron concentration peak when the boron ion implantation energy is 300 keV is [[on the]] positioned deeper than the phosphor concentration peak of the N-well by about 0.3 micrometers. Also, it could be understood that a boron concentration peak when the boron ion implantation energy is 500 keV is ~~on the~~ positioned deeper than the phosphor concentration peak of the N-well by about 0.8 micrometers. Therefore, a sufficient effect of punchthrough prevention is achieved in the

structure of the P-well 4, in which the boron concentration peak is located ~~[[on a]]~~ positioned deeper than the phosphor concentration peak of the N-wells 2 and 3 by about 0.3 to 0.8 micrometers.

Please amend the paragraph beginning at page 11, line 10, as follows:

Next, a relation of the distance between the N-wells 2 and 3 ~~in micrometer~~ and the boron peak concentration is discussed to prevent a punchthrough between the N-wells 2 and 3 ~~sufficiently~~. It could be understood from Fig. 7 that the boron concentration peak are approximately the same in case of the dose quantity of boron of $1E12 /cm^2$ and the ion implantation energy of 300 keV and the boron concentration peak in case of the dose quantity of $1E12 /cm^2$ and the ion implantation energy of 500 keV ~~are approximately same~~.

Please amend the paragraph beginning at page 12, line 1, as follows:

When the relation of the minimum necessary interval is in micrometers, between the N-wells 2 and 3, ~~[[and]]~~ the boron peak concentration is approximated by a straight line of the following equation on the logarithm coordinate as show in Fig. 8 by a broken line,
$$np = (1-s) * 1.4E16 \text{ (atom/cm}^4\text{) (atom/cm}^3\text{)}.$$